

FQP9N90C/FQPF9N90C

900V N-Channel MOSFET

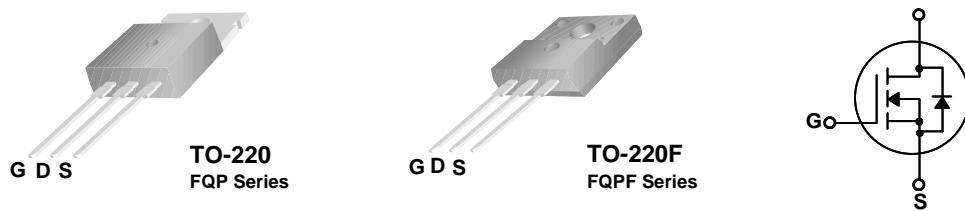
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies.

Features

- 8.0 A, 900V, $R_{DS(on)} = 1.4 \Omega @ V_{GS} = 10 \text{ V}$
- Low gate charge (typical 45nC)
- Low C_{rss} (typical 14pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP9N90C	FQPF9N90C	Units
V_{DSS}	Drain-Source Voltage	900		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	8.0	8.0 *	A
	- Continuous ($T_C = 100^\circ\text{C}$)	2.8	2.8 *	A
I_{DM}	Drain Current - Pulsed	(Note 1)	32	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	900	mJ
I_{AR}	Avalanche Current	(Note 1)	8.0	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	20.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	205	68	W
	- Derate above 25°C	1.64	0.54	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP9N90C	FQPF9N90C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.61	1.85	$^\circ\text{C}/\text{W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	900	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	--	0.99	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 900 \text{ V}$, $V_{GS} = 0 \text{ V}$	--	--	10	μA
		$V_{DS} = 720 \text{ V}$, $T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30 \text{ V}$, $V_{DS} = 0 \text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}$, $V_{DS} = 0 \text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	3.0	--	5.0	V
$R_{DS(\text{on})}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 4 \text{ A}$	--	1.12	1.4	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}$, $I_D = 4 \text{ A}$ (Note 4)	--	9.2	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$	--	2100	2730	pF
C_{oss}	Output Capacitance		--	175	230	pF
C_{rss}	Reverse Transfer Capacitance		--	14	18	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 450 \text{ V}$, $I_D = 9.0 \text{ A}$, $R_G = 25 \Omega$	--	50	110	ns
t_r	Turn-On Rise Time		--	120	250	ns
$t_{d(off)}$	Turn-Off Delay Time		--	100	210	ns
t_f	Turn-Off Fall Time		--	75	160	ns
Q_g	Total Gate Charge	$V_{DS} = 720 \text{ V}$, $I_D = 9.0 \text{ A}$, $V_{GS} = 10 \text{ V}$	--	45	58	nC
Q_{gs}	Gate-Source Charge		--	13	--	nC
Q_{gd}	Gate-Drain Charge		--	18	--	nC
			(Note 4, 5)			

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	8.0	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	32.0	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = 8 \text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}$, $I_S = 9 \text{ A}$	--	550	--	ns
Q_{rr}	Reverse Recovery Charge	$dI_F / dt = 100 \text{ A}/\mu\text{s}$	(Note 4)	--	6.5	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 21 \text{ mH}$, $I_{AS} = 9 \text{ A}$, $V_{DD} = 50 \text{ V}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 9.0 \text{ A}$, $dI/dt \leq 200 \text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300 \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

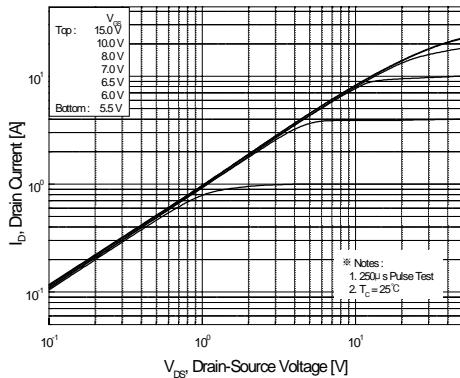


Figure 1. On-Region Characteristics

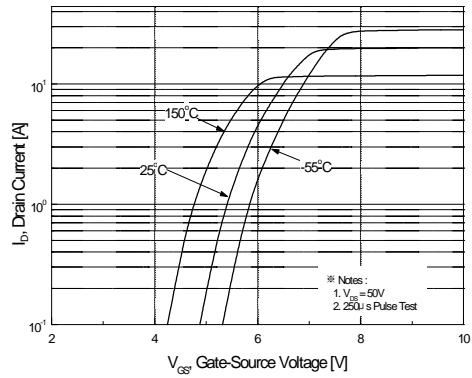


Figure 2. Transfer Characteristics

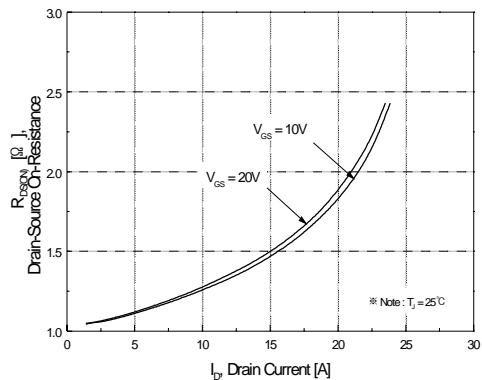


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

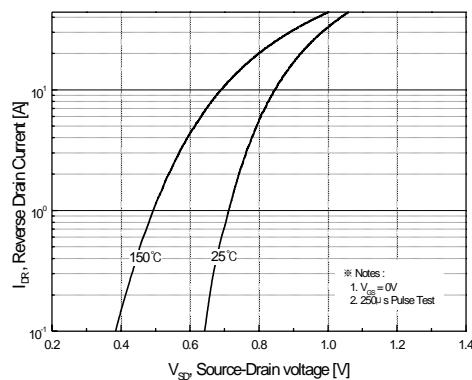


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

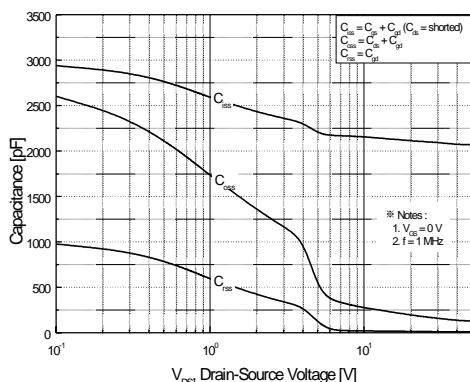


Figure 5. Capacitance Characteristics

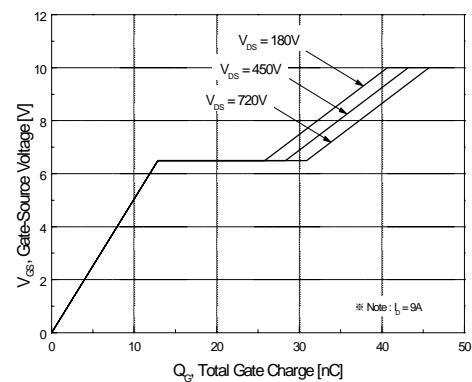


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

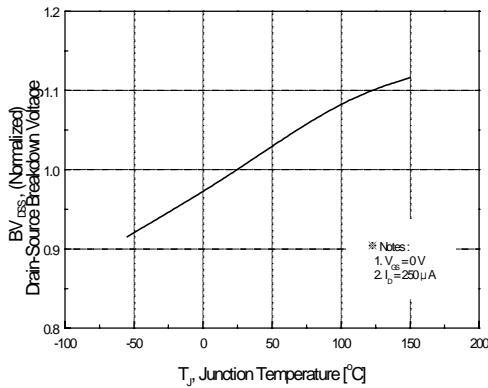


Figure 7. Breakdown Voltage Variation vs Temperature

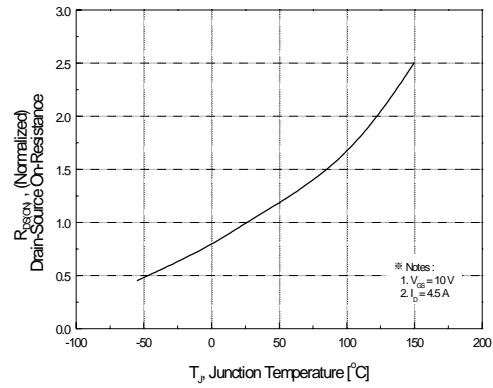


Figure 8. On-Resistance Variation vs Temperature

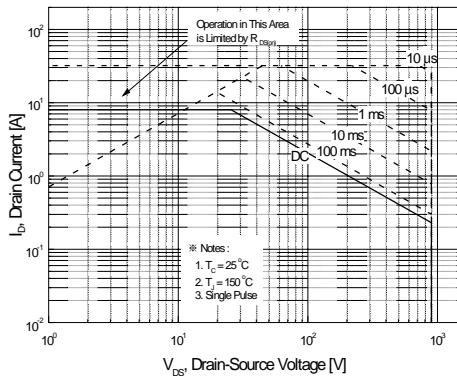


Figure 9-1. Maximum Safe Operating Area for FQP9N90C

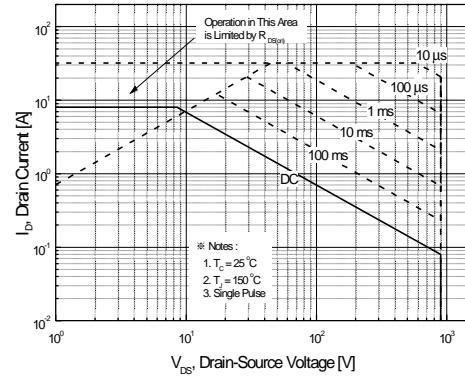


Figure 9-2. Maximum Safe Operating Area for FQPF9N90C

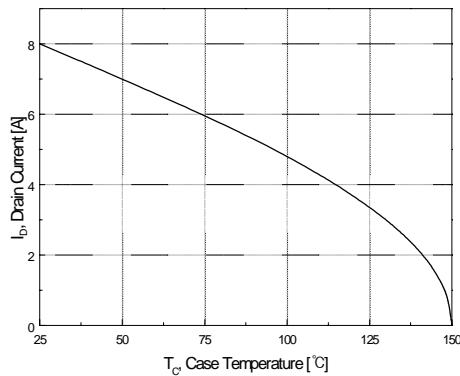


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

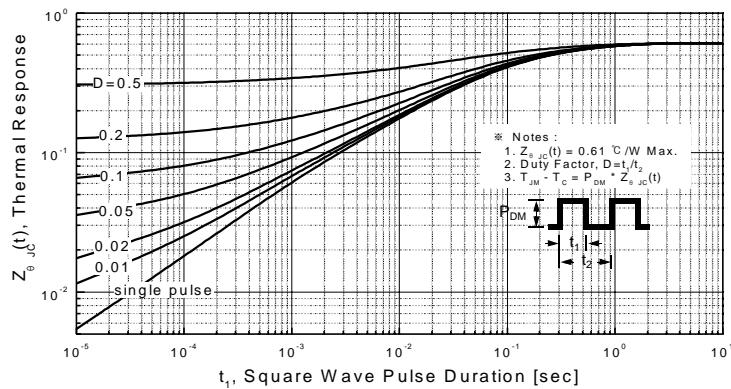


Figure 11-1. Transient Thermal Response Curve for FQP9N90C

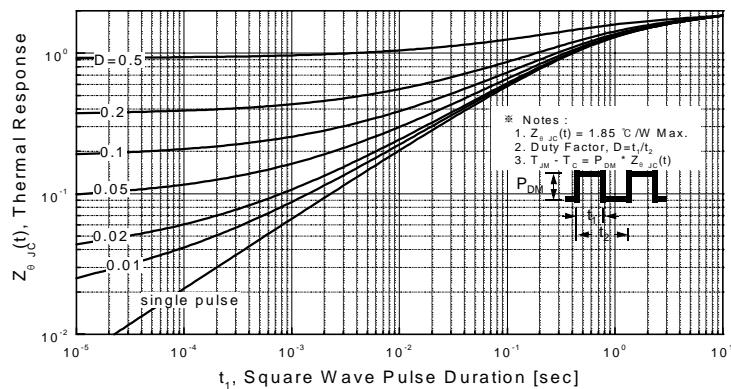
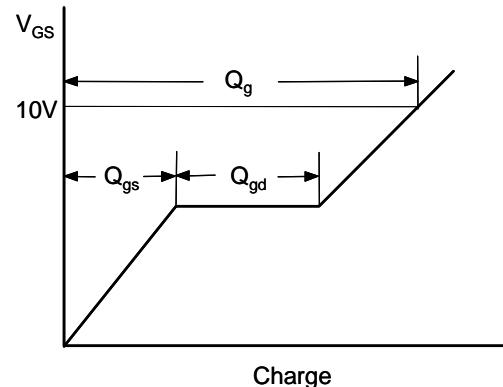
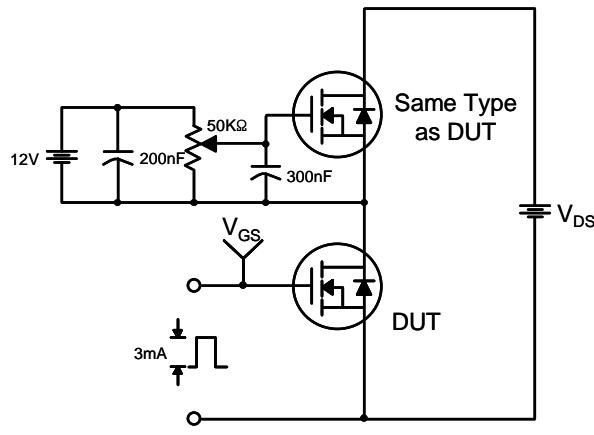
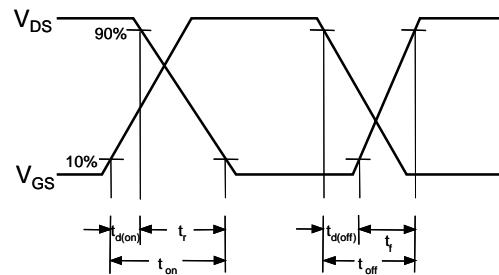
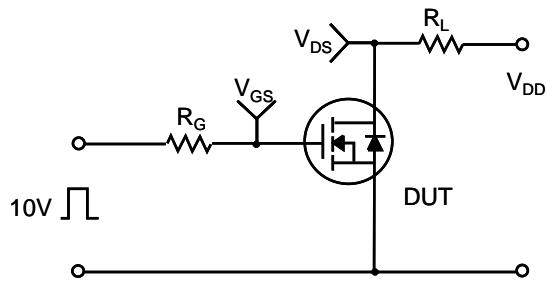


Figure 11-2. Transient Thermal Response Curve for FQPF9N90C

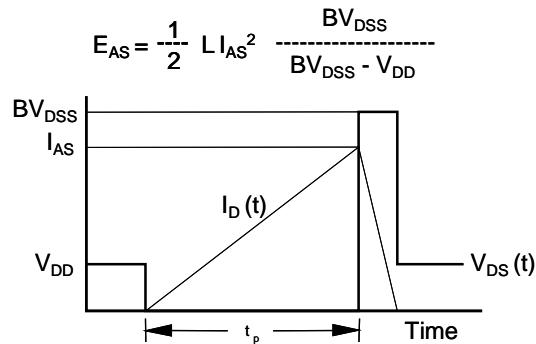
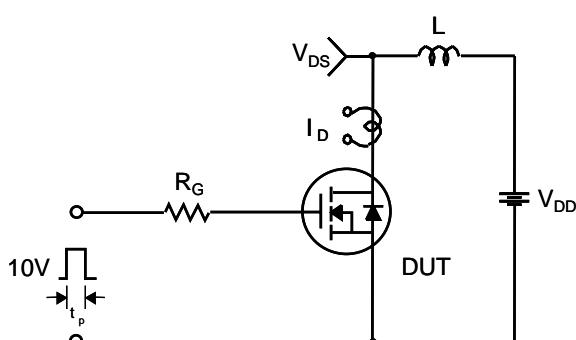
Gate Charge Test Circuit & Waveform



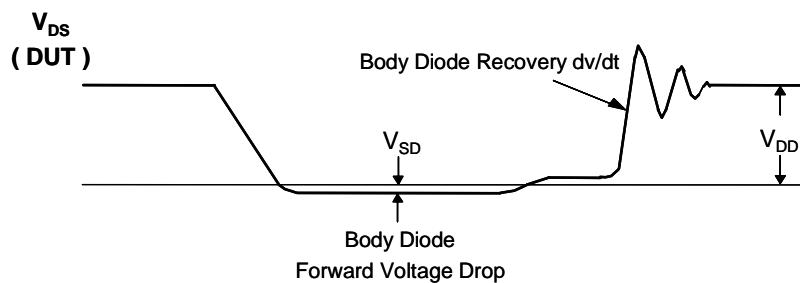
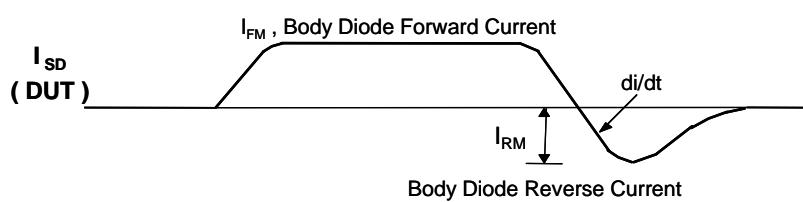
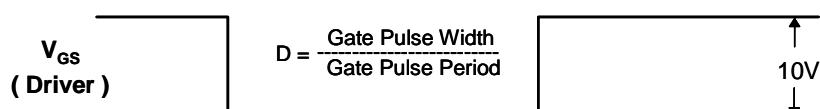
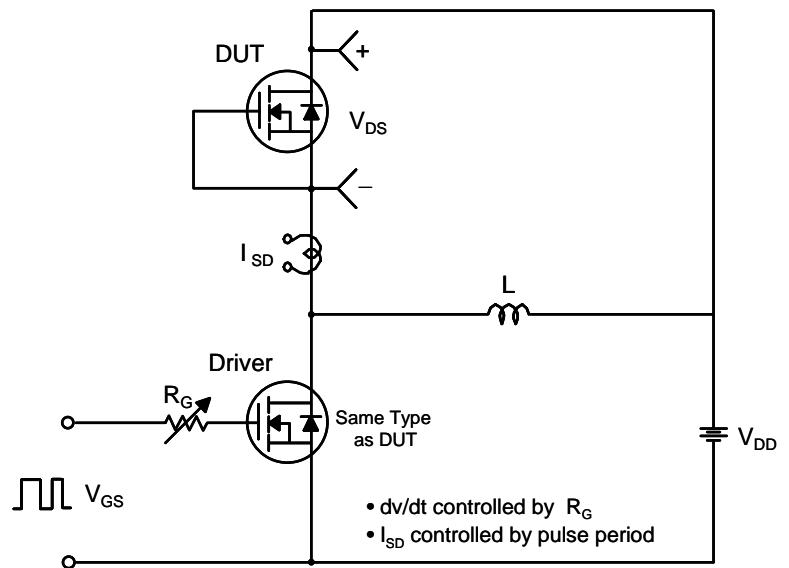
Resistive Switching Test Circuit & Waveforms

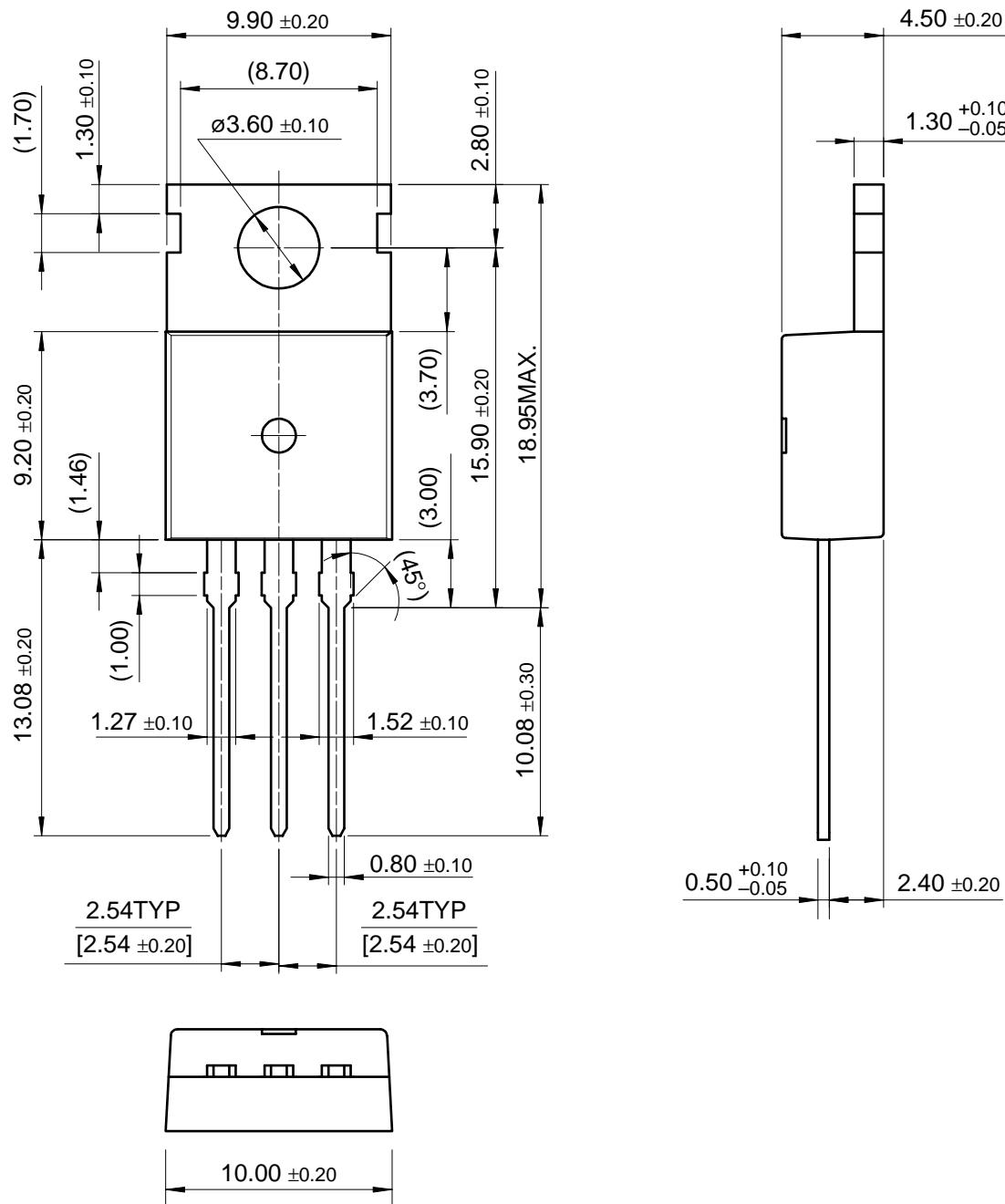


Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms

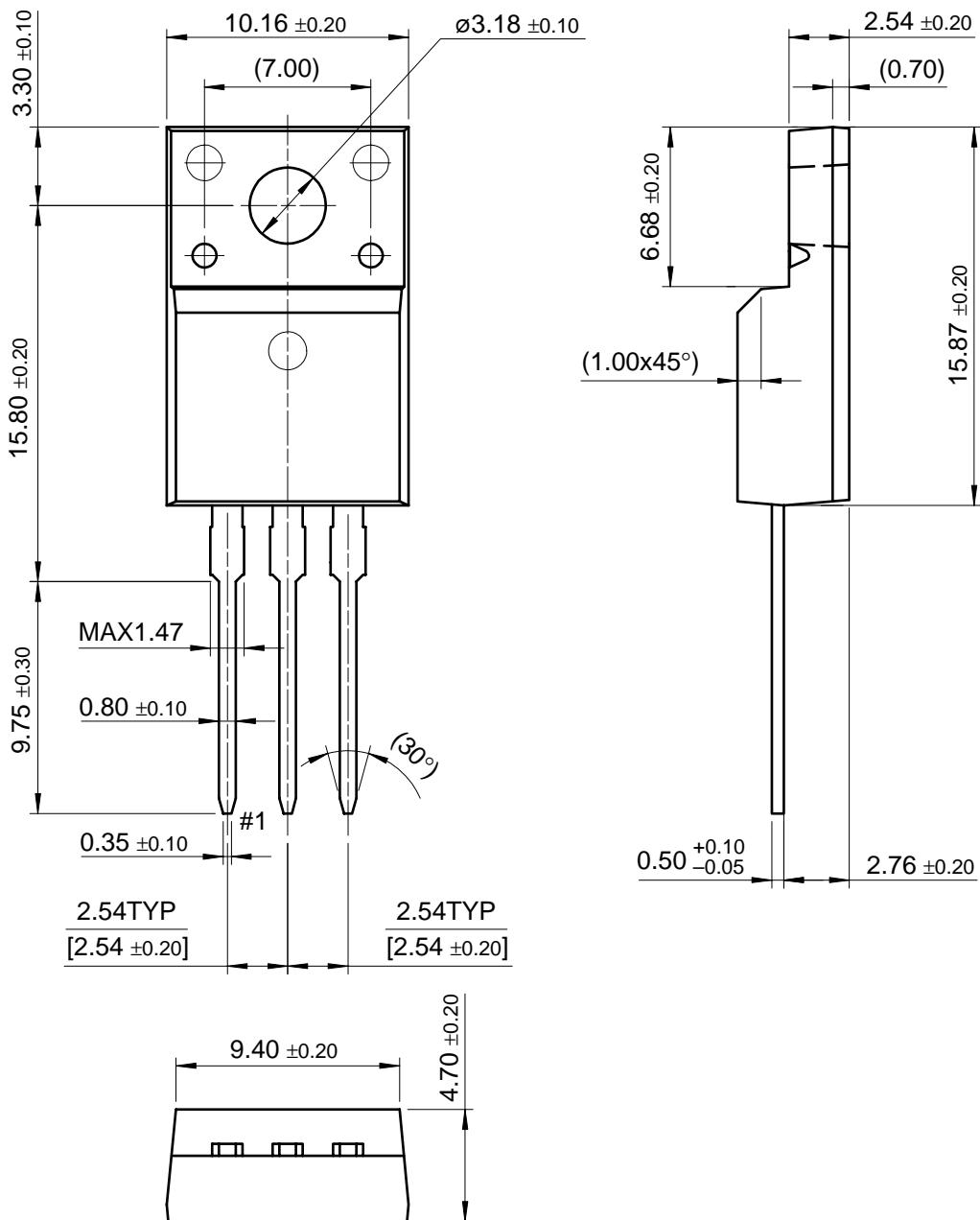


Package Dimensions**TO-220**

Dimensions in Millimeters

Package Dimensions (Continued)

TO-220F



Dimensions in Millimeters

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